Abstracts

Cryogenically Cooled GaAs FET Amplifier with a Noise Temperature Under 70 K at 5.0 GHz (Short Papers)

J. Pierro. "Cryogenically Cooled GaAs FET Amplifier with a Noise Temperature Under 70 K at 5.0 GHz (Short Papers)." 1976 Transactions on Microwave Theory and Techniques 24.12 (Dec. 1976 [T-MTT] (1976 Symposium Issue)): 972-975.

A 4.5-5.0-GHz gallium arsenide field-effect transistor (GaAs FET) amplifier cryogenically cooled to approximately 70 K is described. A noise temperature of under 70 K is achieved over the hand. Power gain for the two-stage amplifier is 20 dB. A noise analysis is performed to predict noise-temperature dependence on the temperature of the amplifier.

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